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roducts	Home ▶ 2N5634 (#23412) 2N5634 (#23412)							Related Links			
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	Electrical Rating	Symbol	Min	ı Ty	/p Max	٢	Unit	Sales Contacts RFQ/Samples			
	Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.0	D	V	Kru/Samples			
	DC Current Gain	HFE	15.	00	60.0	00					
	Maximum Electrical Rating		ymbol	Min	Тур Ма		Unit				
	Breakdown Voltage, Collector-Base (Emitter Open)		V _{BR(CBO)}				V				
	Collector Current (dc)						A				
	Collector-Emitter Voltage (Base Open)	_	CEO			140.00 V 7.00 V 150.00 W					
	Emitter-Base Voltage (Collector Open) Power Dissipation, Total	P									
	 This part can be found in the following product Discretes > Transistors > BJT(BiPolar Junction Transistors > Bartian Non-Radiation Hardened Devices > Transistors > Tradiation Hardened Devices > Transistors > Tran	nsistor) 🕨	PNP Trar		r)) NPN	Transi	stor				

